V23990-P588-A61-PM

preliminary datasheet

*flow*PIM 1 3rd gen — 1200 V/15 A

Features

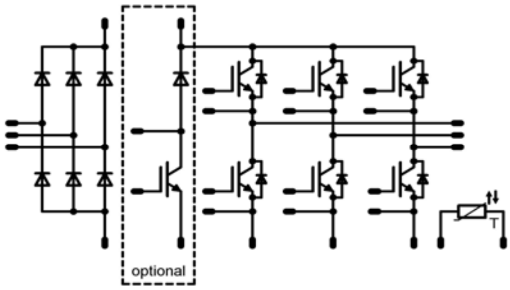
- 3~ rectifier, opt. BRC, Inverter, NTC
- Very compact housing, easy to route
- IGBT3 / Emitter Controller Diode 3 technology

flow 1 housing

Target Applications

- Motor Drives

Schematic



Types

- V23990-P588-A61-PM

Maximum Ratings

T_j=25°C, unless otherwise specified

Parameter	Symbol	Condition		Value	Unit
Input Rectifier Diode					
Repetitive peak reverse voltage	V_{RRM}			1600	V
DC forward current	I_{FAV}	$T_j=T_j max$	T_h=80°C T_c=80°C	36 49	A
Surge forward current	I_{FSM}	t_p=10ms	T_j=25°C	370	A
I^2t-value	I^2t			680	A^2s
Power dissipation per Diode	P_{tot}	$T_j=T_j max$	T_h=80°C T_c=80°C	42 64	W
Maximum Junction Temperature	$T_j max$			150	°C
Inverter Transistor					
Collector-emitter break down voltage	V_{CE}			1200	V
DC collector current	I_C	$T_j=T_j max$	T_h=80°C T_c=80°C	19 24	A
Repetitive peak collector current	I_{Cpulse}	t_p limited by $T_j max$		45	A
Turn off safe operating area		VCE ≤ 1200V, Tj ≤ Top max		45	A
Power dissipation per IGBT	P_{tot}	$T_j=T_j max$	T_h=80°C T_c=80°C	47 72	W
Gate-emitter peak voltage	V_{GE}			±20	V
Short circuit ratings	t_{SC} V_{CC}	T_j≤150°C V_{GE}=15V		10 1200	μs V
Maximum Junction Temperature	$T_j max$			150	°C

Maximum Ratings

T_j=25°C, unless otherwise specified

Parameter	Symbol	Condition		Value	Unit
Inverter Diode					
Peak Repetitive Reverse Voltage	V_{RRM}	T_j=25°C		1200	V
DC forward current	I_F	T_j=$T_j$max	T_h=80°C T_c=80°C	17 22	A
Repetitive peak forward current	I_{FRM}	t_p limited by $T_j$max		30	A
Power dissipation per Diode	P_{tot}	T_j=$T_j$max	T_h=80°C T_c=80°C	31 48	W
Maximum Junction Temperature	$T_j$max			150	°C
Brake Transistor					
Collector-emitter break down voltage	V_{CE}			1200	V
DC collector current	I_C	T_j=$T_j$max	T_h=80°C T_c=80°C	14 16	A
Repetitive peak collector current	I_{Cpuls}	t_p limited by $T_j$max		24	A
Turn off safe operating area		VCE ≤ 1200V, Tj ≤ Top max		24	A
Power dissipation per IGBT	P_{tot}	T_j=$T_j$max	T_h=80°C T_c=80°C	38 58	W
Gate-emitter peak voltage	V_{GE}			±20	V
Short circuit ratings	t_{SC} V_{CC}	T_j≤150°C V_{GE}=15V		10 1200	μs V
Maximum Junction Temperature	$T_j$max			150	°C
Brake Diode					
Peak Repetitive Reverse Voltage	V_{RRM}	T_j=25°C		1200	V
DC forward current	I_F	T_j=$T_j$max	T_h=80°C T_c=80°C	15 15	A
Repetitive peak forward current	I_{FRM}	t_p limited by $T_j$max		15	A
Power dissipation per Diode	P_{tot}	T_j=$T_j$max	T_h=80°C T_c=80°C	36 55	W
Maximum Junction Temperature	$T_j$max			150	°C
Thermal Properties					
Storage temperature	T_{stg}			-40…+125	°C
Operation temperature under switching condition	T_{op}			-40…+(Tjmax - 25)	°C
Insulation Properties					
Insulation voltage	V_{is}	t=2s	DC voltage	4000	V
Creepage distance				min 12,7	mm
Clearance				min 12,7	mm
Comparative tracking index	CTI			>200	

Characteristic Values

Parameter	Symbol	Conditions					Value			Unit
			V_{GE} [V] or V_{GS} [V]	V_r [V] or V_{CE} [V] or V_{DS} [V]	I_C [A] or I_F [A] or I_D [A]	T_j	Min	Typ	Max	
Input Rectifier Diode										
Forward voltage	V_F				35	Tj=25°C Tj=125°C	0,8	1,20 1,16	1,55	V
Threshold voltage (for power loss calc. only)	V_{to}				35	Tj=25°C Tj=125°C		0,91 0,79		V
Slope resistance (for power loss calc. only)	r_t				35	Tj=25°C Tj=125°C		8,27 10,61		mΩ
Reverse current	I_r			1600		Tj=25°C Tj=125°C			0,05	mA
Thermal resistance chip to heatsink per chip	R_{thJH}	Thermal grease thickness≤50um λ = 1 W/mK						1,66		K/W
Thermal resistance chip to heatsink per chip	R_{thJC}							1,09		
Inverter Transistor										
Gate emitter threshold voltage	$V_{GE(th)}$	$V_{CE}=V_{GE}$			0,0006	Tj=25°C Tj=125°C	5	5,8	6,5	V
Collector-emitter saturation voltage	$V_{CE(sat)}$		15		15	Tj=25°C Tj=125°C	1,35	1,86 2,11	2,05	V
Collector-emitter cut-off current incl. Diode	I_{CES}		0	1200		Tj=25°C Tj=125°C			0,002	mA
Gate-emitter leakage current	I_{GES}		20	0		Tj=25°C Tj=125°C			120	nA
Integrated Gate resistor	R_{gint}							none		Ω
Turn-on delay time	$t_{d(on)}$	Rgoff=54 Ω Rgon=54 Ω	±15	600	15	Tj=25°C Tj=125°C		48 46		ns
Rise time	t_r					Tj=25°C Tj=125°C		27 33		
Turn-off delay time	$t_{d(off)}$					Tj=25°C Tj=125°C		348 424		
Fall time	t_f					Tj=25°C Tj=125°C		121 221		
Turn-on energy loss per pulse	E_{on}					Tj=25°C Tj=125°C		1,54 2,04		mWs
Turn-off energy loss per pulse	E_{off}					Tj=25°C Tj=125°C		1,06 1,66		
Input capacitance	C_{ies}	f=1MHz	0	25		Tj=25°C		1090		pF
Output capacitance	C_{oss}							58		
Reverse transfer capacitance	C_{rss}							48		
Gate charge	Q_{Gate}		±15	960	40	Tj=25°C		72		nC
Thermal resistance chip to heatsink per chip	R_{thJH}	Thermal grease thickness≤50um λ = 1 W/mK						1,47		K/W
Thermal resistance chip to case per chip	R_{thJC}							0,97		
Inverter Diode										
Diode forward voltage	V_F				15	Tj=25°C Tj=125°C	1	1,73 1,73	2,4	V
Peak reverse recovery current	I_{RRM}	Rgon=54 Ω	±15	600	15	Tj=25°C Tj=125°C		11,5 13,54		A
Reverse recovery time	t_{rr}					Tj=25°C Tj=125°C		476,6 651,3		ns
Reverse recovered charge	Q_{rr}					Tj=25°C Tj=125°C		2,03 3,38		μC
Peak rate of fall of recovery current	di(rec)max /dt					Tj=25°C Tj=125°C		91 36		A/μs
Reverse recovered energy	Erec					Tj=25°C Tj=125°C		0,77 1,35		mWs
Thermal resistance chip to heatsink per chip	R_{thJH}	Thermal grease thickness≤50um λ = 1 W/mK						2,23		K/W
Thermal resistance chip to case per chip	R_{thJC}							1,47		

Characteristic Values

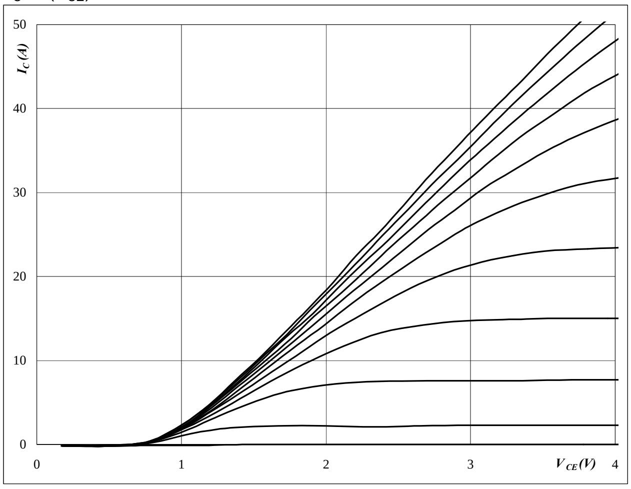
Parameter	Symbol	Conditions					Value			Unit
			V_{GE} [V] or V_{GS} [V]	V_r [V] or V_{CE} [V] or V_{DS} [V]	I_C [A] or I_F [A] or I_D [A]	T_j	Min	Typ	Max	
Brake Transistor										
Gate emitter threshold voltage	$V_{GE(th)}$	$V_{CE}=V_{GE}$			0,0003	Tj=25°C Tj=125°C	5	5,8	6,5	V
Collector-emitter saturation voltage	$V_{CE(sat)}$		15		8	Tj=25°C Tj=125°C		1,73 1,85		V
Collector-emitter cut-off incl diode	I_{CES}		0	1200		Tj=25°C Tj=125°C			0,05	mA
Gate-emitter leakage current	I_{GES}		20	0		Tj=25°C Tj=125°C			120	nA
Integrated Gate resistor	R_{gint}							none		Ω
Turn-on delay time	$t_{d(on)}$	Rgoff=81 Ω Rgon=81 Ω	±15	600	8	Tj=25°C Tj=125°C		44 46		ns
Rise time	t_r					Tj=25°C Tj=125°C		20 24		
Turn-off delay time	$t_{d(off)}$					Tj=25°C Tj=125°C		305 375		
Fall time	t_f					Tj=25°C Tj=125°C		113 181		
Turn-on energy loss per pulse	E_{on}					Tj=25°C Tj=125°C		0,64 0,82		mWs
Turn-off energy loss per pulse	E_{off}					Tj=25°C Tj=125°C		0,54 0,83		
Input capacitance	C_{ies}	f=1MHz	0	25		Tj=25°C		605		pF
Output capacitance	C_{oss}							37		
Reverse transfer capacitance	C_{rss}							29		
Gate charge	Q_{Gate}		15	960	8	Tj=25°C		52		nC
Thermal resistance chip to heatsink per chip	R_{thJH}	Thermal grease thickness≤50um λ = 1 W/mK						1,83		K/W
Thermal resistance chip to case per chip	R_{thJC}							1,21		
Brake Diode										
Diode forward voltage	V_F				7,5	Tj=25°C Tj=125°C	1	1,42 1,34	2,3	V
Reverse leakage current	I_r	Rgon=81 Ω		1200		Tj=25°C Tj=125°C			250	μA
Peak reverse recovery current	I_{RRM}	Rgon=81 Ω Rgon=81 Ω	±15	600	7,5	Tj=25°C Tj=125°C		8,1 9,2		A
Reverse recovery time	t_{rr}					Tj=25°C Tj=125°C		396,2 574,5		ns
Reverse recovered charge	Q_{rr}					Tj=25°C Tj=125°C		1,11 1,11		μC
Peak rate of fall of recovery current	di(rec)max /dt					Tj=25°C Tj=125°C		88 56		A/μs
Reverse recovery energy	E_{rec}					Tj=25°C Tj=125°C		0,45 0,71		mWs
Thermal resistance chip to heatsink per chip	R_{thJH}	Thermal grease thickness≤50um λ = 1 W/mK						1,93		K/W
Thermal resistance chip to case per chip	R_{thJC}							1,27		
Thermistor										
Rated resistance	R					T=25°C		22000		Ω
Deviation of R100	ΔR/R	R100=1486 Ω				T=100°C	-5		5	%
R100	P					T=100°C		210		mW
Power dissipation constant						T=25°C		3,5		mW/K
A-value	$B_{(25/50)}$	Tol. ±3%				T=25°C				K
B-value	$B_{(25/100)}$	Tol. ±3%				T=25°C		4000		K
Vincotech NTC Reference									A	
Module Properties										
Thermal resistance, case to heatsink	R_{thCH}							tbd.		K/W
Module stray inductance	L_{sCE}							5		nH
Chip module lead resistance, terminals -chip	$R_{cc'1+EE'}$							tbd.		mΩ
Mounting torque	M						3,8	4	4,2	Nm
Terminal connection torque	M						6,7	7	7,4	Nm
Weight	G							tbd.		g

Output Inverter

Figure 1 Output inverter IGBT

Typical output characteristics

$I_C = f(V_{CE})$



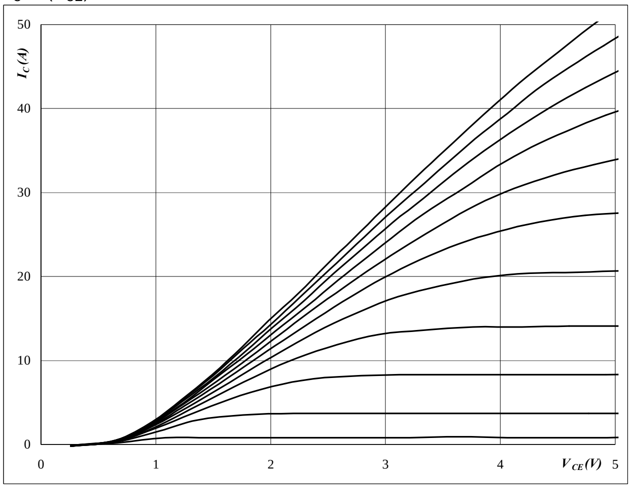
At

t_p =	250	µs
T_j =	25	°C
V_{GE} from	7 V to 17 V in steps of 1 V	

Figure 2 Output inverter IGBT

Typical output characteristics

$I_C = f(V_{CE})$



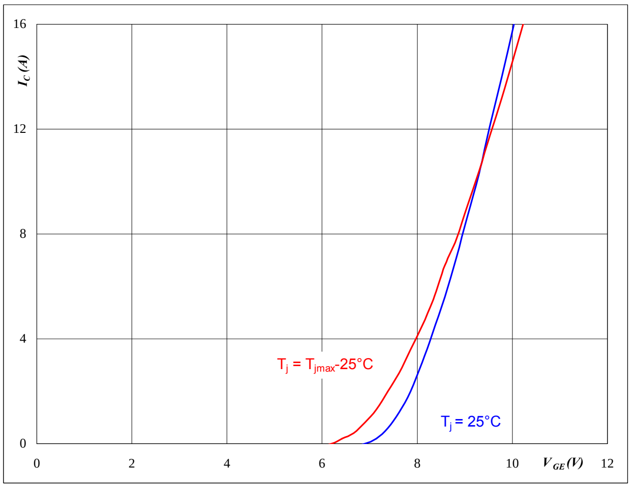
At

t_p =	250	µs
T_j =	125	°C
V_{GE} from	7 V to 17 V in steps of 1 V	

Figure 3 Output inverter IGBT

Typical transfer characteristics

$I_C = f(V_{GE})$



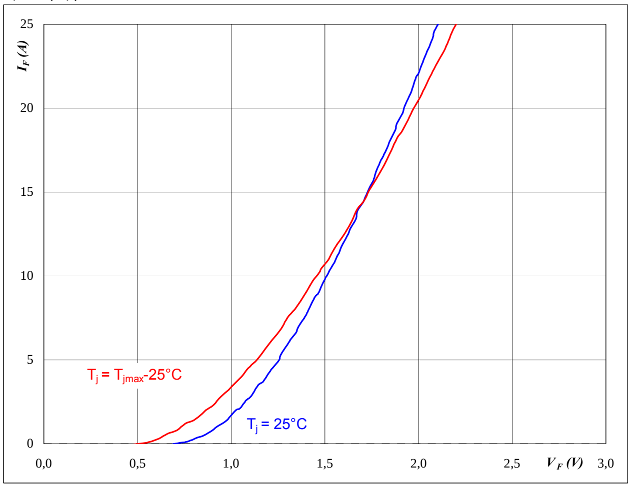
At

t_p =	250	µs
V_{CE} =	10	V

Figure 4 Output inverter FWD

Typical diode forward current as a function of forward voltage

$I_F = f(V_F)$



At

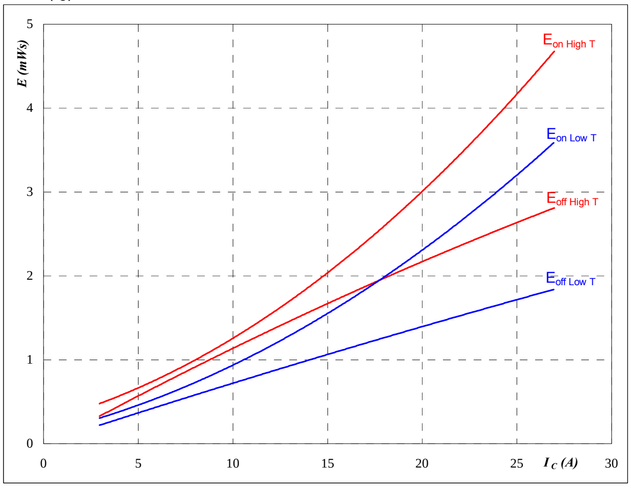
t_p =	250	µs

Output Inverter

Figure 5 Output inverter IGBT

Typical switching energy losses as a function of collector current

$E = f(I_C)$



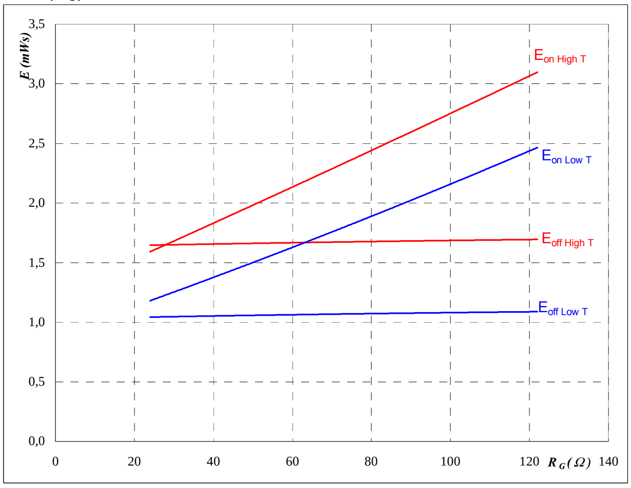
With an inductive load at

T_j =	25/125	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	54	Ω
R_{goff} =	54	Ω

Figure 6 Output inverter IGBT

Typical switching energy losses as a function of gate resistor

$E = f(R_G)$



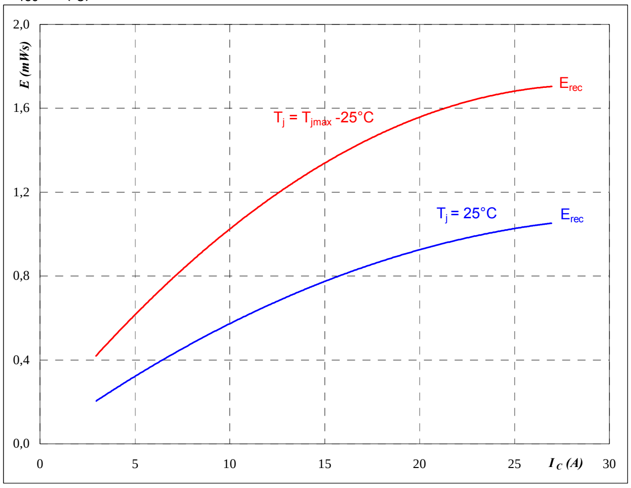
With an inductive load at

T_j =	25/125	°C
V_{CE} =	600	V
V_{GE} =	±15	V
I_C =	15	A

Figure 7 Output inverter FWD

Typical reverse recovery energy loss as a function of collector current

$E_{rec} = f(I_C)$



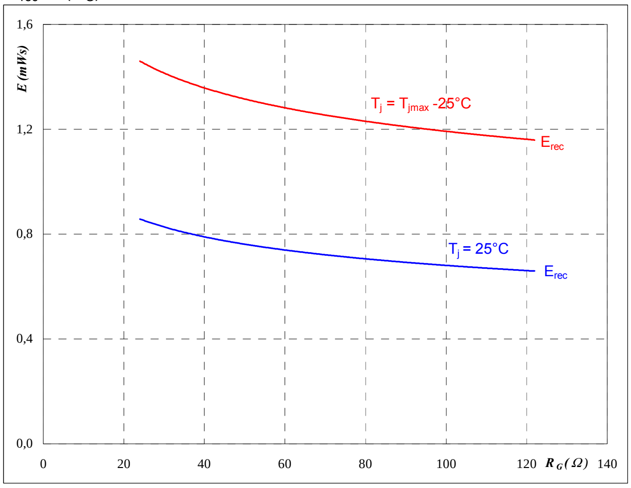
With an inductive load at

T_j =	25/125	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	54	Ω

Figure 8 Output inverter FWD

Typical reverse recovery energy loss as a function of gate resistor

$E_{rec} = f(R_G)$



With an inductive load at

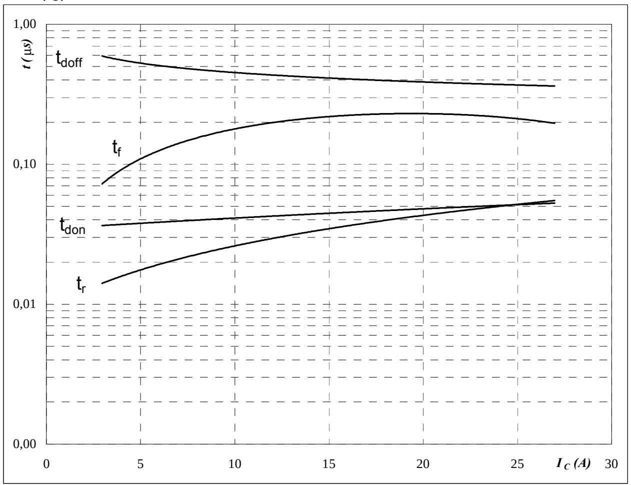
T_j =	25/125	°C
V_{CE} =	600	V
V_{GE} =	±15	V
I_C =	15	A

Output Inverter

Figure 9 Output inverter IGBT

Typical switching times as a function of collector current

t = f(I_C)



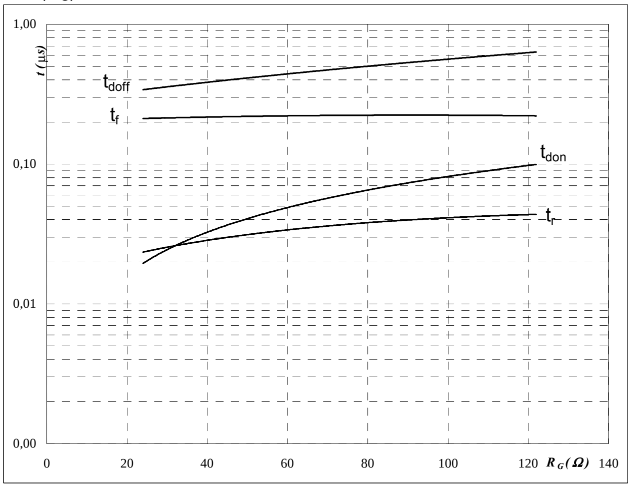
With an inductive load at

T_j =	125	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	54	Ω
R_{goff} =	54	Ω

Figure 10 Output inverter IGBT

Typical switching times as a function of gate resistor

t = f(R_G)



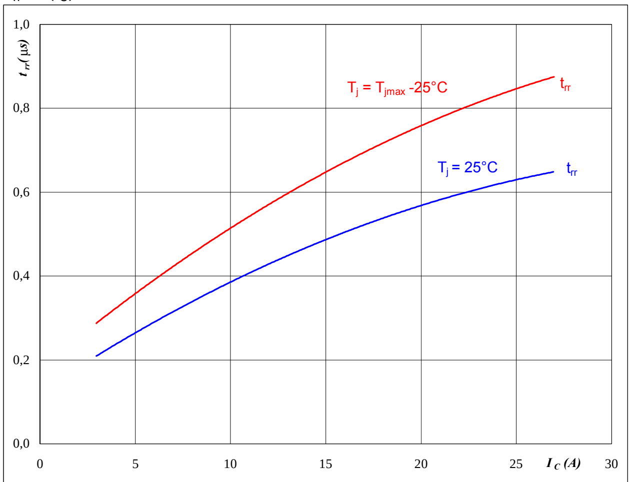
With an inductive load at

T_j =	125	°C
V_{CE} =	600	V
V_{GE} =	±15	V
I_C =	15	A

Figure 11 Output inverter FWD

Typical reverse recovery time as a function of collector current

t_{rr} = f(I_C)



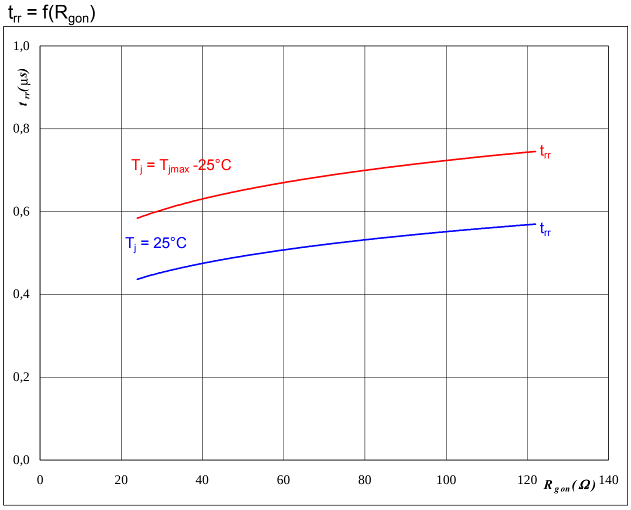
At

T_j =	25/125	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	54	Ω

Figure 12 Output inverter FWD

Typical reverse recovery time as a function of IGBT turn on gate resistor

t_{rr} = f(R_{gon})



At

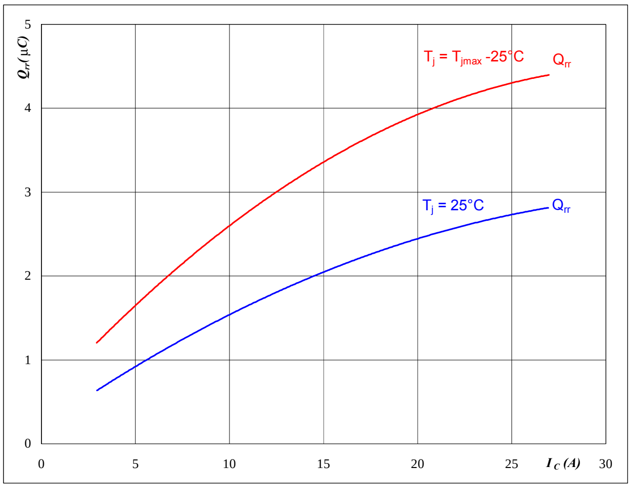
T_j =	25/125	°C
V_R =	600	V
I_F =	15	A
V_{GE} =	±15	V

Output Inverter

Figure 13 Output inverter FWD

Typical reverse recovery charge as a function of collector current

$Q_{rr} = f(I_C)$



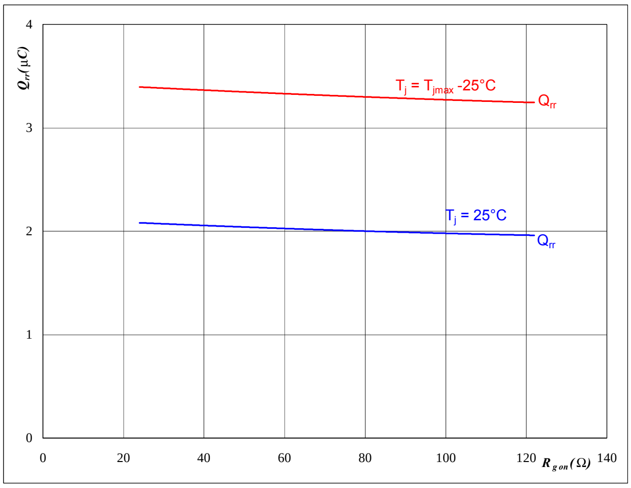
At

T_j =	25/125	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	54	Ω

Figure 14 Output inverter FWD

Typical reverse recovery charge as a function of IGBT turn on gate resistor

$Q_{rr} = f(R_{gon})$



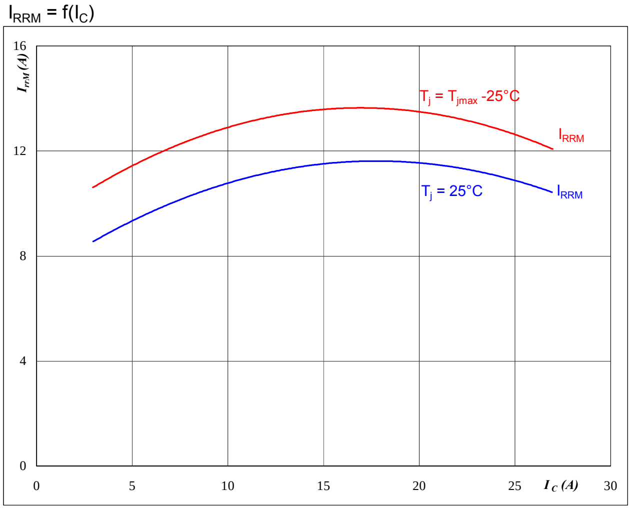
At

T_j =	25/125	°C
V_R =	600	V
I_F =	15	A
V_{GE} =	±15	V

Figure 15 Output inverter FWD

Typical reverse recovery current as a function of collector current

$I_{RRM} = f(I_C)$



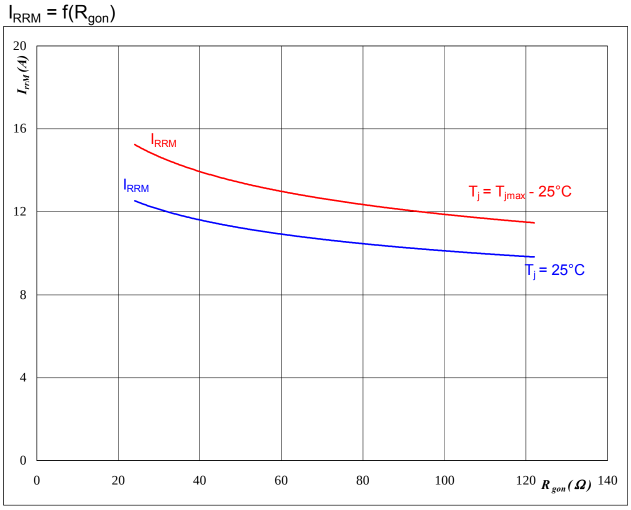
At

T_j =	25/125	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	54	Ω

Figure 16 Output inverter FWD

Typical reverse recovery current as a function of IGBT turn on gate resistor

$I_{RRM} = f(R_{gon})$



At

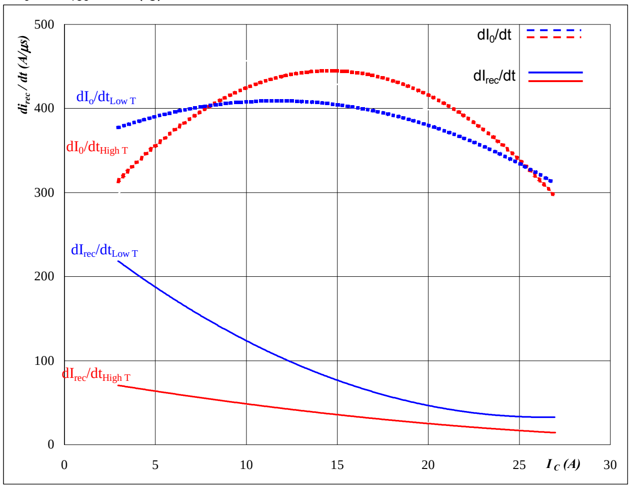
T_j =	25/125	°C
V_R =	600	V
I_F =	15	A
V_{GE} =	±15	V

Output Inverter

Figure 17 — Output inverter FWD

Typical rate of fall of forward and reverse recovery current as a function of collector current

$dI_0/dt, dI_{rec}/dt = f(I_C)$



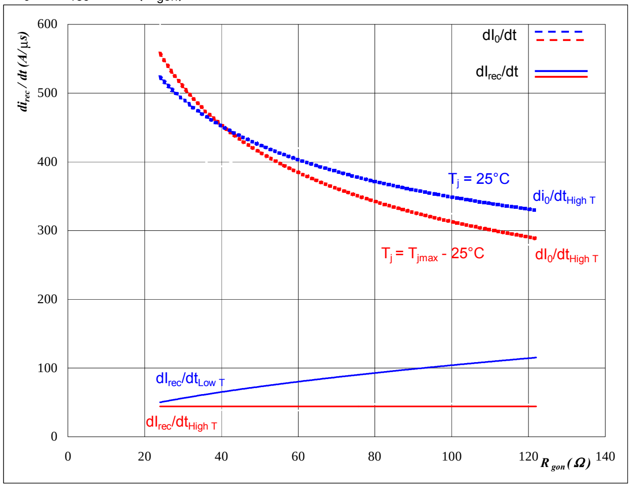
At

T_j =	25/125	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	54	Ω

Figure 18 — Output inverter FWD

Typical rate of fall of forward and reverse recovery current as a function of IGBT turn on gate resistor

$dI_0/dt, dI_{rec}/dt = f(R_{gon})$



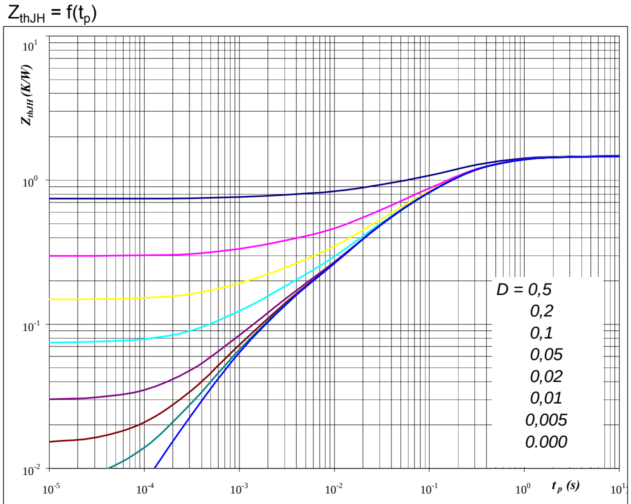
At

T_j =	25/125	°C
V_R =	600	V
I_F =	15	A
V_{GE} =	±15	V

Figure 19 — Output inverter IGBT

IGBT transient thermal impedance as a function of pulse width

$Z_{thJH} = f(t_p)$



At

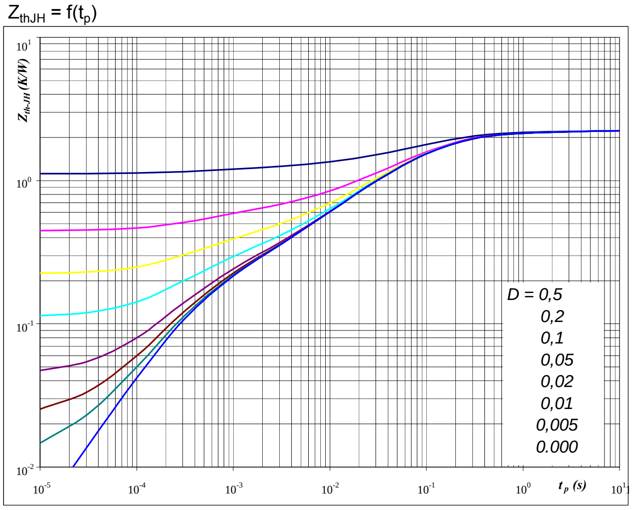
D = t_p / T

R_{thJH} = 1,47 K/W RthJH = 1,43 K/W

Figure 20 — Output inverter FWD

FWD transient thermal impedance as a function of pulse width

$Z_{thJH} = f(t_p)$



At

D = t_p / T

R_{thJH} = 2,23 K/W RthJH = 2,16 K/W

IGBT thermal model values

Thermal grease R (C/W)	Thermal grease Tau (s)	Phase change interface R (C/W)	Phase change interface Tau (s)
0,03	2,3E+01	0,03	2,3E+01
0,12	1,2E+00	0,11	1,2E+00
0,50	2,8E-01	0,49	2,8E-01
0,51	9,0E-02	0,50	8,7E-02
0,24	1,6E-02	0,23	1,5E-02
0,08	1,3E-03	0,08	1,3E-03

FWD thermal model values

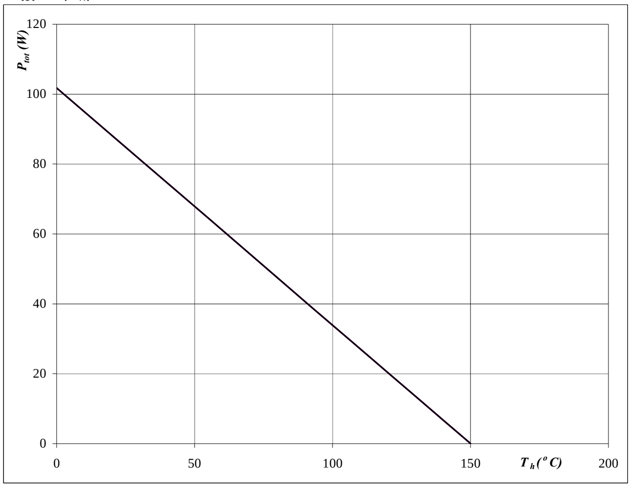
Thermal grease R (C/W)	Thermal grease Tau (s)	Phase change interface R (C/W)	Phase change interface Tau (s)
0,11	3,0E+00	0,10	2,9E+00
0,34	3,7E-01	0,33	3,6E-01
1,07	8,4E-02	1,04	8,2E-02
0,42	1,7E-02	0,40	1,7E-02
0,16	2,7E-03	0,15	2,6E-03
0,14	3,8E-04	0,14	3,6E-04

Output Inverter

Figure 21 Output inverter IGBT

Power dissipation as a function of heatsink temperature

$P_{tot} = f(T_h)$



At

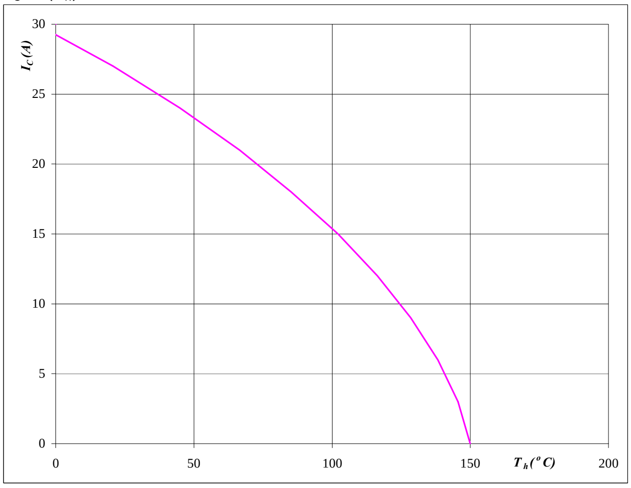
T_j = 150 °C

single heating
overall heating

Figure 22 Output inverter IGBT

Collector current as a function of heatsink temperature

$I_C = f(T_h)$



At

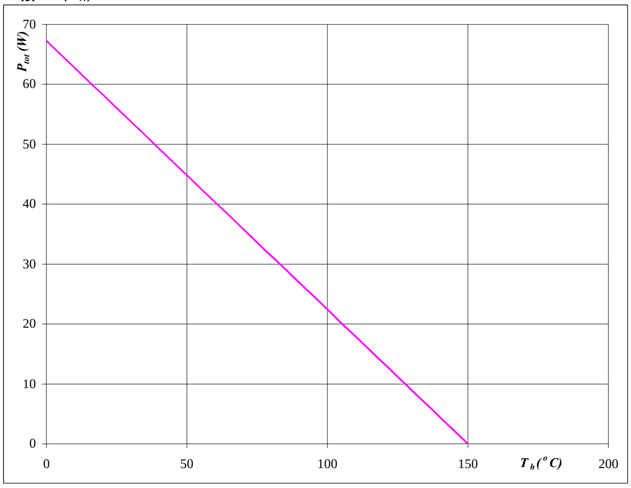
T_j = 150 °C

V_{GE} = 15 V

Figure 23 Output inverter FWD

Power dissipation as a function of heatsink temperature

$P_{tot} = f(T_h)$



At

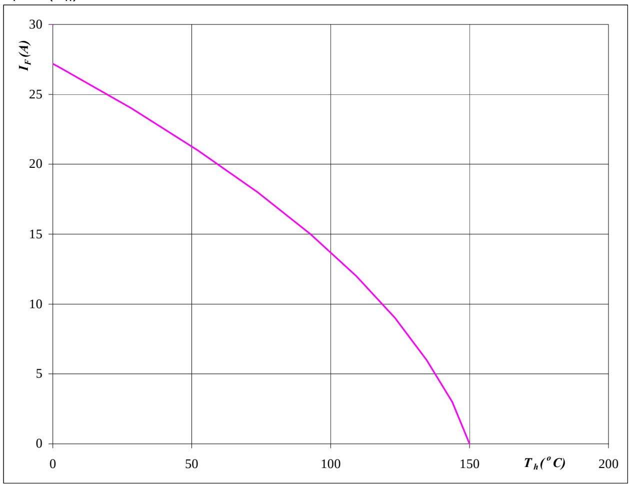
T_j = 150 °C

single heating
overall heating

Figure 24 Output inverter FWD

Forward current as a function of heatsink temperature

$I_F = f(T_h)$



At

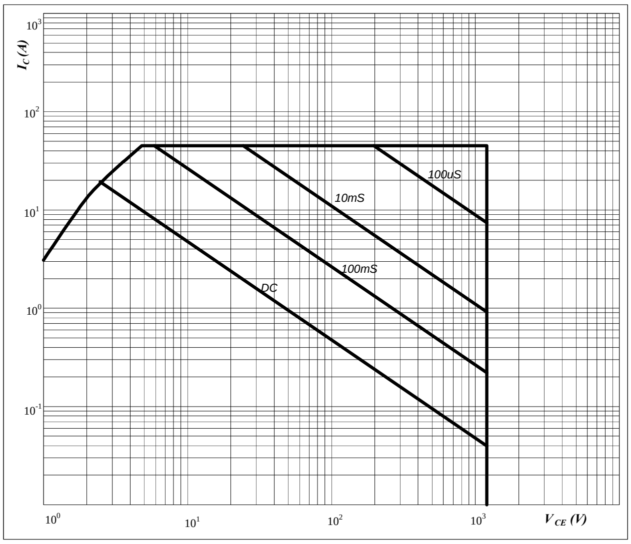
T_j = 150 °C

Output Inverter

Figure 25 Output inverter IGBT

Safe operating area as a function of collector-emitter voltage

$I_C = f(V_{CE})$



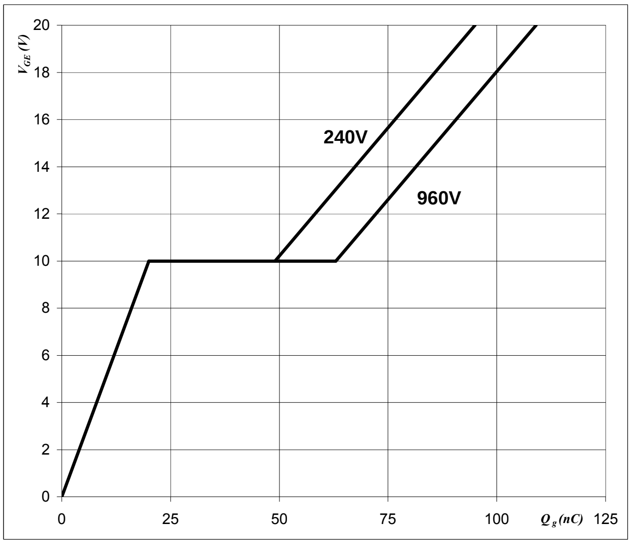
At

D =	single pulse	
T_h =	80	ºC
V_{GE} =	±15	V
T_j =	T_{jmax}	ºC

Figure 26 Output inverter IGBT

Gate voltage vs Gate charge

$V_{GE} = f(Q_{GE})$



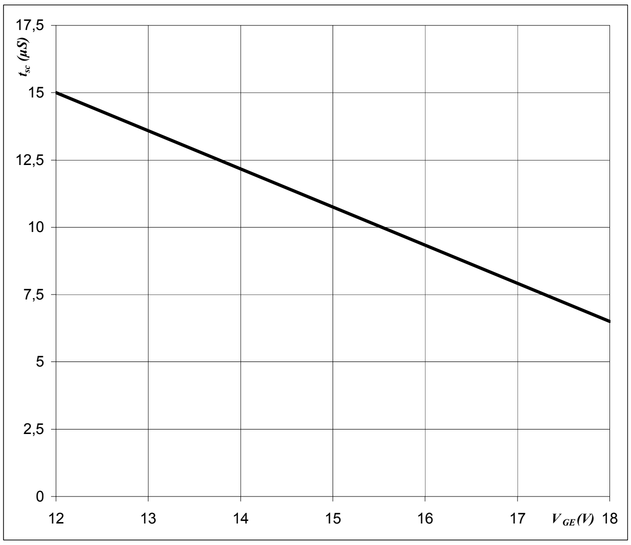
At

I_C =	15	A

Figure 27 Output inverter IGBT

Short circuit withstand time as a function of gate-emitter voltage

$t_{sc} = f(V_{GE})$



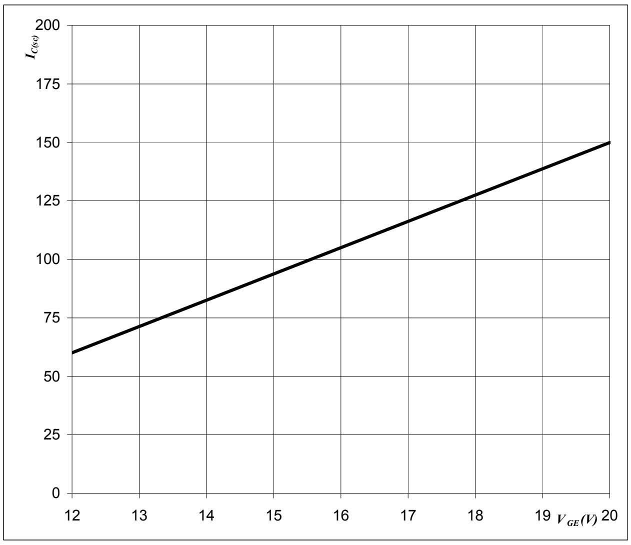
At

V_{CE} =	1200	V
T_j ≤	150	ºC

Figure 28 Output inverter IGBT

Typical short circuit collector current as a function of gate-emitter voltage

$V_{GE} = f(Q_{GE})$



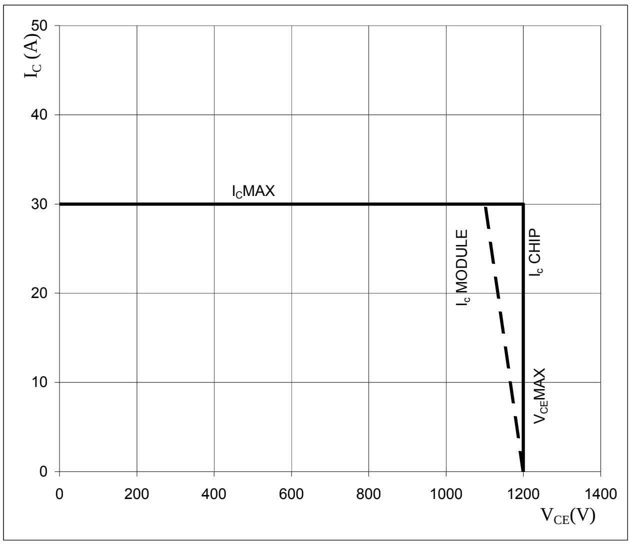
At

V_{CE} ≤	1200	V
T_j =	150	ºC

Figure 29 IGBT

Reverse bias safe operating area

$I_C = f(V_{CE})$



At

T_j = T_{jmax}-25 ºC

$U_{ccminus}$=U_{ccplus}

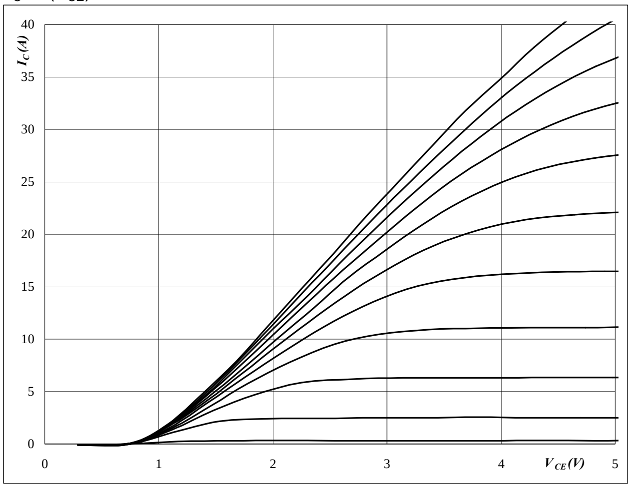
Switching mode : 3 level switching

Brake

Figure 1 Brake IGBT

Typical output characteristics

$I_C = f(V_{CE})$



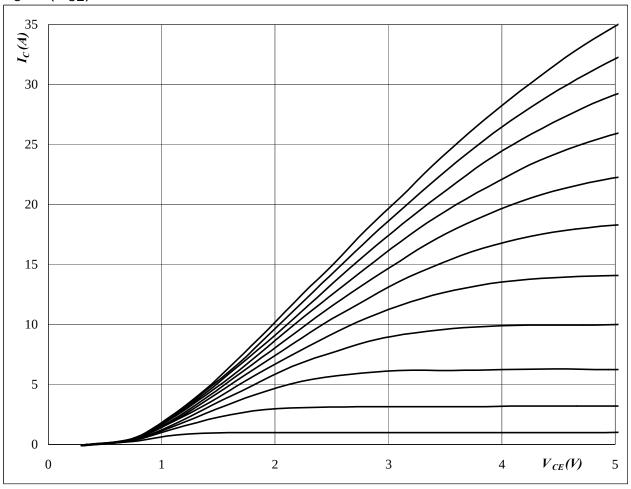
At

t_p =	250	µs
T_j =	25	°C
V_{GE} from	7 V to 17 V in steps of 1 V	

Figure 2 Brake IGBT

Typical output characteristics

$I_C = f(V_{CE})$



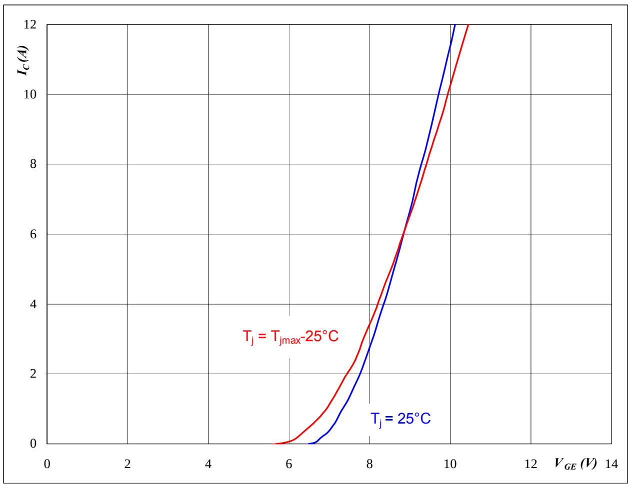
At

t_p =	250	µs
T_j =	125	°C
V_{GE} from	7 V to 17 V in steps of 1 V	

Figure 3 Brake IGBT

Typical transfer characteristics

$I_C = f(V_{GE})$



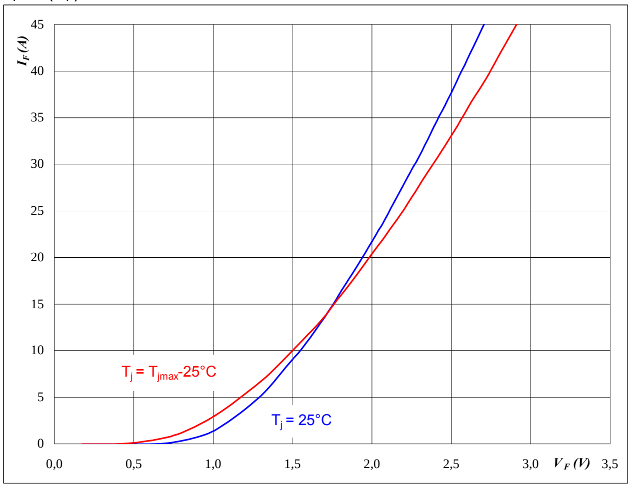
At

t_p =	250	µs
V_{CE} =	10	V

Figure 4 Brake FWD

Typical diode forward current as a function of forward voltage

$I_F = f(V_F)$



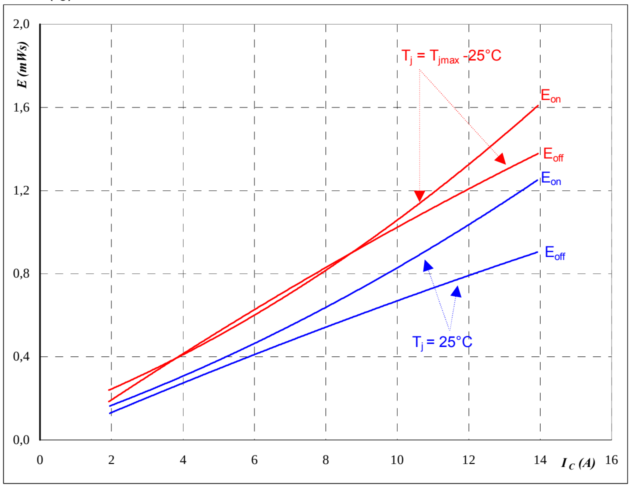
At

t_p =	250	µs

Brake

Figure 5 Brake IGBT

Typical switching energy losses
as a function of collector current
$E = f(I_C)$

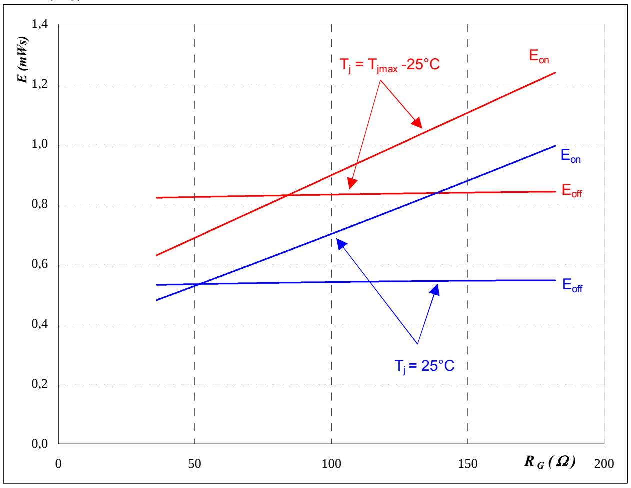


With an inductive load at

T_j =	25/125	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	81	Ω
R_{goff} =	81	Ω

Figure 6 Brake IGBT

Typical switching energy losses
as a function of gate resistor
$E = f(R_G)$

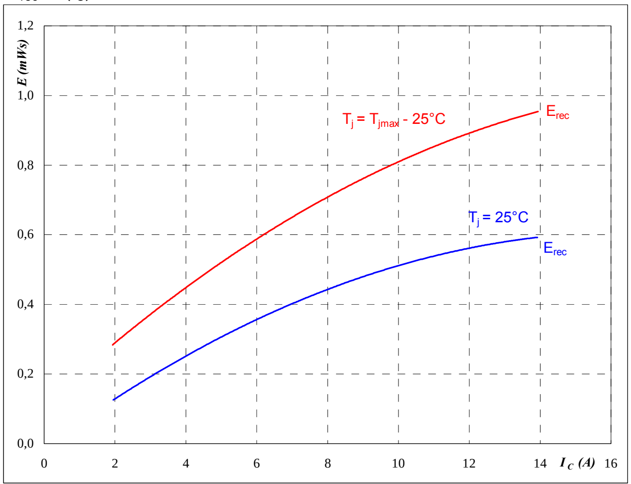


With an inductive load at

T_j =	25/125	°C
V_{CE} =	600	V
V_{GE} =	±15	V
I_C =	8	A

Figure 7 Brake FWD

Typical reverse recovery energy loss
as a function of collector current
$E_{rec} = f(I_C)$

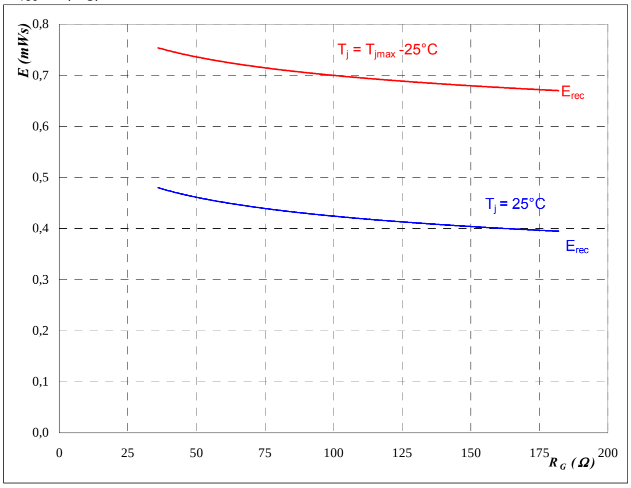


With an inductive load at

T_j =	25/125	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	81	Ω

Figure 8 Brake FWD

Typical reverse recovery energy loss
as a function of gate resistor
$E_{rec} = f(R_G)$



With an inductive load at

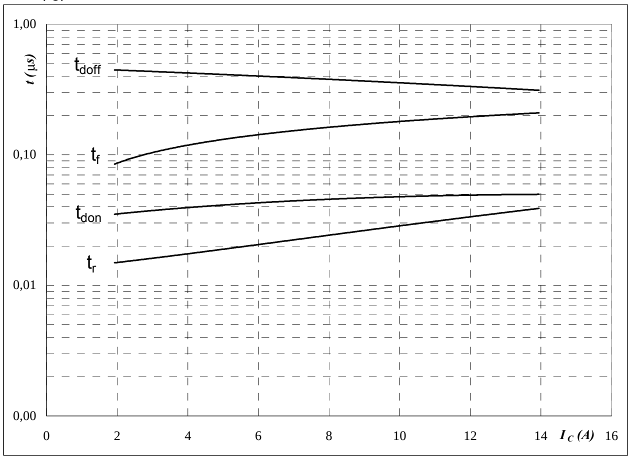
T_j =	25/125	°C
V_{CE} =	600	V
V_{GE} =	±15	V
I_C =	8	A

Brake

Figure 9 Brake IGBT

Typical switching times as a function of collector current

$t = f(I_C)$



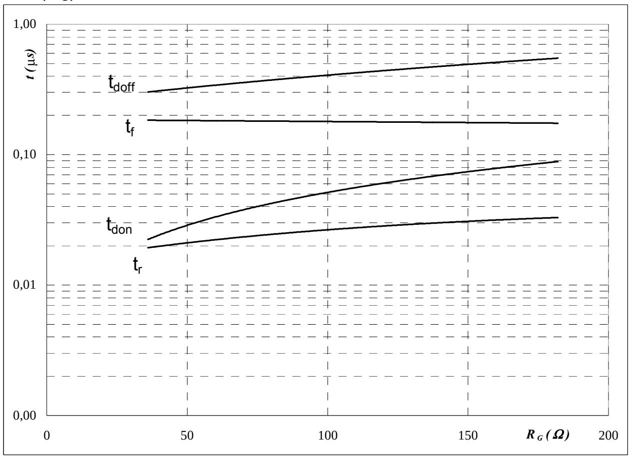
With an inductive load at

T_j =	25/125	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	81	Ω
R_{goff} =	81	Ω

Figure 10 Brake IGBT

Typical switching times as a function of gate resistor

$t = f(R_G)$



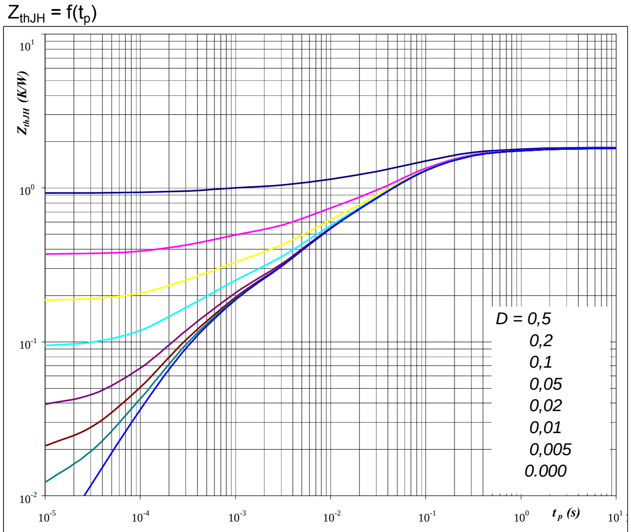
With an inductive load at

T_j =	25/125	°C
V_{CE} =	600	V
V_{GE} =	±15	V
I_C =	8	A

Figure 11 Brake IGBT

IGBT transient thermal impedance as a function of pulse width

$Z_{thJH} = f(t_p)$

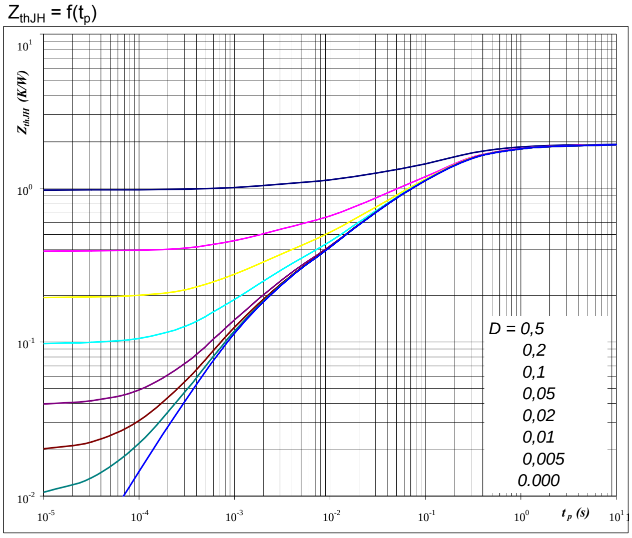


At		D =	tp / T		
Thermal grease			Phase change interface		
R_{thJH} =	1,830	K/W	R_{thJH} =	0,60	K/W

Figure 12 Brake FWD

FWD transient thermal impedance as a function of pulse width

$Z_{thJH} = f(t_p)$



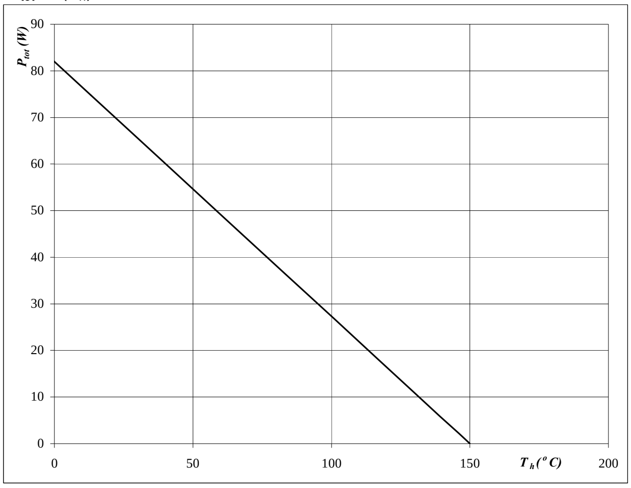
At		D =	tp / T		
Thermal grease			Phase change interface		
R_{thJH} =	1,93	K/W	R_{thJH} =	1,27	K/W

Brake

Figure 13 Brake IGBT

Power dissipation as a function of heatsink temperature

$P_{tot} = f(T_h)$



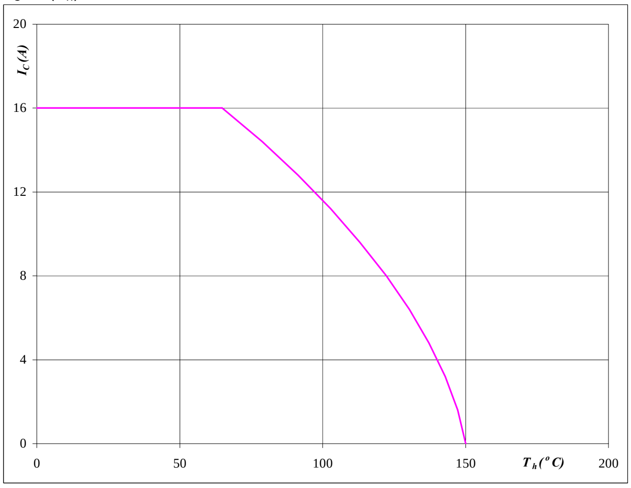
At

T_j = 150 ºC

Figure 14 Brake IGBT

Collector current as a function of heatsink temperature

$I_C = f(T_h)$



At

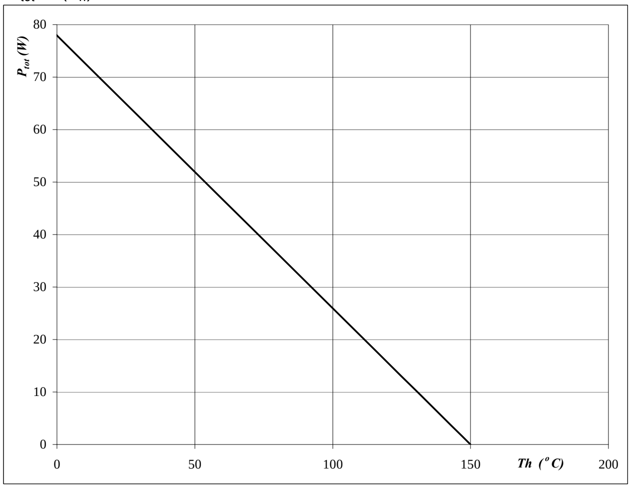
T_j = 150 ºC

V_{GE} = 15 V

Figure 15 Brake FWD

Power dissipation as a function of heatsink temperature

$P_{tot} = f(T_h)$



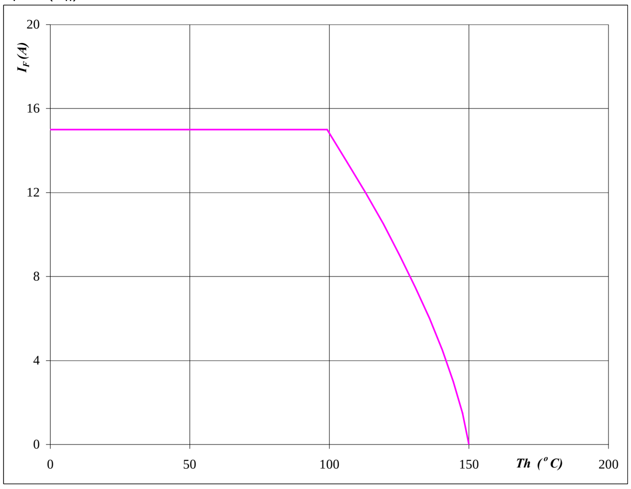
At

T_j = 150 ºC

Figure 16 Brake FWD

Forward current as a function of heatsink temperature

$I_F = f(T_h)$



At

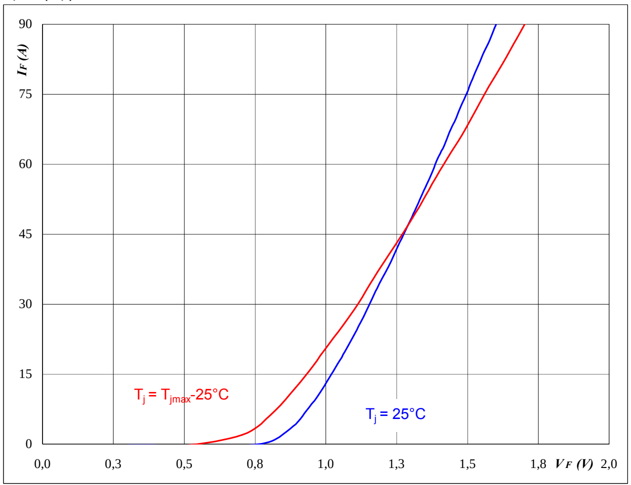
T_j = 150 ºC

Input Rectifier Bridge

Figure 1 Rectifier diode

Typical diode forward current as a function of forward voltage

$I_F = f(V_F)$



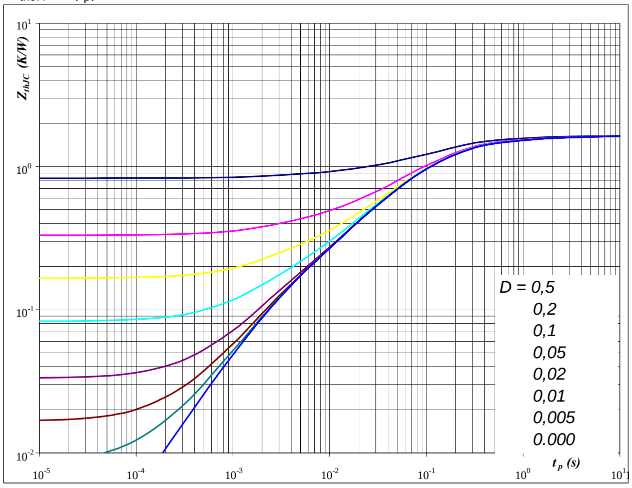
At

t_p = 250 µs

Figure 2 Rectifier diode

Diode transient thermal impedance as a function of pulse width

$Z_{thJH} = f(t_p)$



At

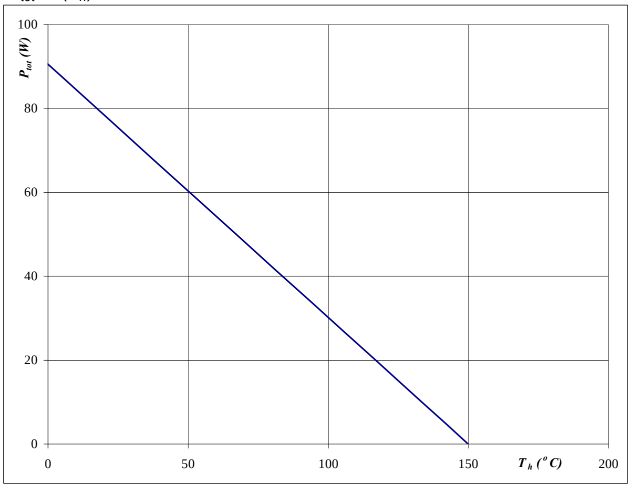
D = t_p / T

R_{thJH} = 1,657 K/W

Figure 3 Rectifier diode

Power dissipation as a function of heatsink temperature

$P_{tot} = f(T_h)$



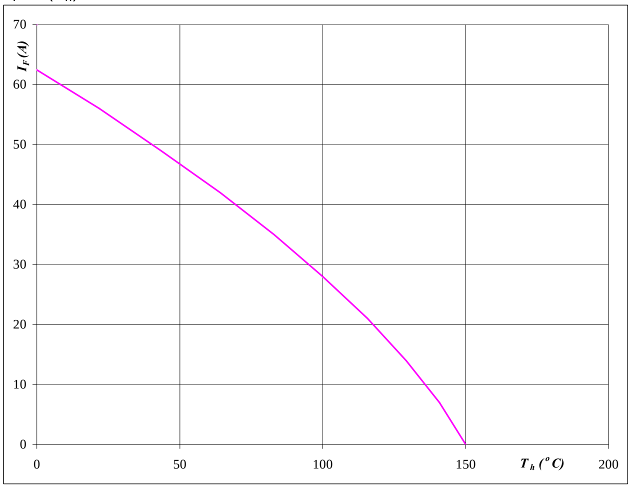
At

T_j = 150 ºC

Figure 4 Rectifier diode

Forward current as a function of heatsink temperature

$I_F = f(T_h)$



At

T_j = 150 ºC

Thermistor

Figure 1 Thermistor

Typical NTC characteristic
as a function of temperature
$R_T = f(T)$

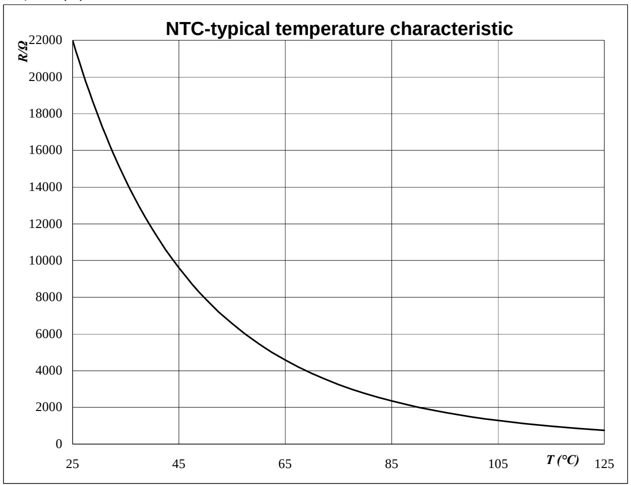


Figure 2 Thermistor

Typical NTC resistance values

$$R(T) = R_{25} \cdot e^{\left(B_{25/100} \cdot \left(\frac{1}{T} - \frac{1}{T_{25}}\right)\right)} \quad [\Omega]$$

T [°C]	R_{nom} [Ω]	R_{min} [Ω]	R_{max} [Ω]	△R/R [±%]
-55	2089434,5	1506495,4	2672373,6	27,9
0	71804,2	59724,4	83884	16,8
10	43780,4	37094,4	50466,5	15,3
20	27484,6	23684,6	31284,7	13,8
25	22000	19109,3	24890,7	13,1
30	17723,3	15512,2	19934,4	12,5
60	5467,9	4980,6	5955,1	8,9
70	3848,6	3546	4151,1	7,9
80	2757,7	2568,2	2947,1	6,9
90	2008,9	1889,7	2128,2	5,9
100	**1486,1**	**1411,8**	**1560,4**	**5**
150	400,2	364,8	435,7	8,8

Ordering Code and Marking - Outline - Pinout

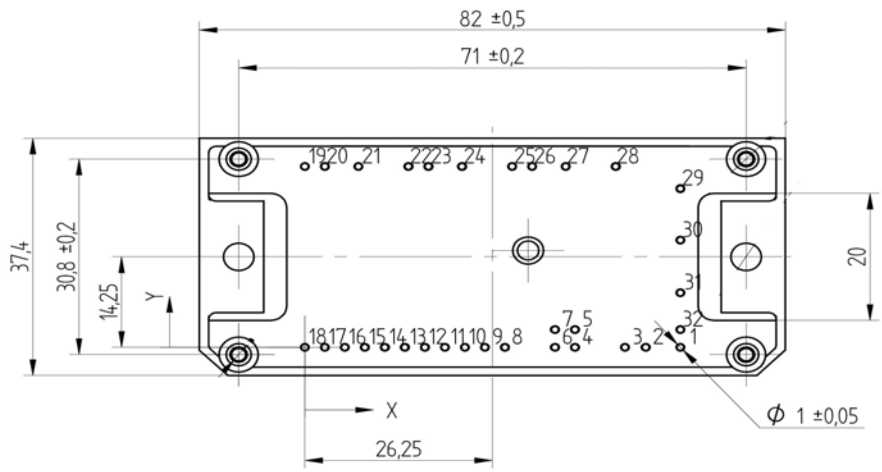
Ordering Code & Marking

Version	Ordering Code	in DataMatrix as	in packaging barcode as
flow1 without thermal paste 17mm housing	V23990-P588-A61-PM	P588-A61	P588-A61

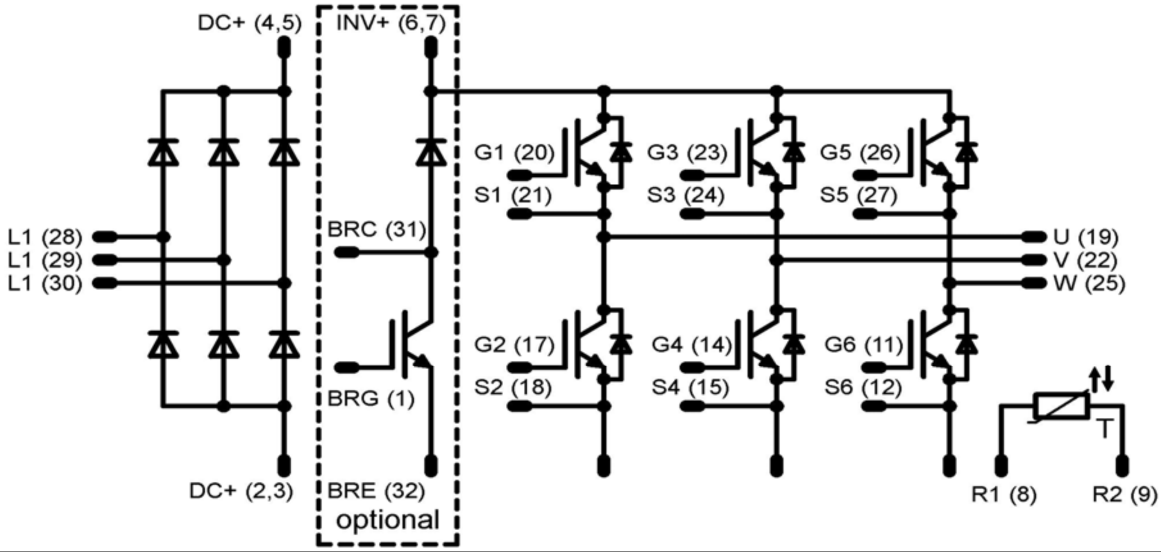
Outline

Pin table

Pin	X	Y
1	52,55	0
2	47,7	0
3	44,8	0
4	37,8	0
5	37,8	2,8
6	35	0
7	35	2,8
8	28	0
9	25,2	0
10	22,4	0
11	19,6	0
12	16,8	0
13	14	0
14	11,2	0
15	8,4	0
16	5,6	0
17	2,8	0
18	0	0
19	0	28,5
20	2,8	28,5
21	7,5	28,5
22	14,5	28,5
23	17,3	28,5
24	22	28,5
25	29	28,5
26	31,8	28,5
27	36,5	28,5
28	43,5	28,5
29	52,55	25
30	52,55	16,9
31	52,55	8,6
32	52,55	2,8



Pinout



PRODUCT STATUS DEFINITIONS

Datasheet Status	Product Status	Definition
Target	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice. The data contained is exclusively intended for technically trained staff.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data may be published at a later date. Vincotech reserves the right to make changes at any time without notice in order to improve design. The data contained is exclusively intended for technically trained staff.
Final	Full Production	This datasheet contains final specifications. Vincotech reserves the right to make changes at any time without notice in order to improve design. The data contained is exclusively intended for technically trained staff.